

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

**Claim 1 (Withdrawn)** A semiconductor device comprising:

- a gallium arsenide substrate;
- a first electrode layer formed on said gallium arsenide substrate;
- a nitride based semiconductor layer formed on said first electrode layer and containing at least one of boron, gallium, aluminum and indium; and
- a second electrode layer formed on said nitride based semiconductor layer.

**Claim 2 (Withdrawn)** The semiconductor device according to claim 1, wherein said nitride based semiconductor layer includes an active layer.

**Claim 3 (Withdrawn)** The semiconductor device according to claim 2, wherein

said nitride based semiconductor layer has a striped current injection region for injecting a current into said active layer, said striped current injection region is formed along a  $\langle 1\bar{1}00 \rangle$  direction of said nitride based semiconductor layer, and said nitride based semiconductor layer is arranged on said gallium arsenide semiconductor such that the  $\langle 1\bar{1}00 \rangle$  direction of said nitride based semiconductor layer coincides with a  $\langle 110 \rangle$  direction or a  $\langle 1\bar{1}0 \rangle$  direction of said gallium arsenide substrate, and a pair of cavity facets is formed of a  $\{110\}$  plane or a  $\{1\bar{1}0\}$  plane of said gallium arsenide substrate and a  $\{1\bar{1}00\}$  plane of said nitride based semiconductor layer.

**Claims 4-11 (Canceled)**

**Claim 12 (Currently Amended)** A semiconductor device comprising:

an insulating substrate;

a first nitride based semiconductor layer formed on said insulating substrate and containing at least one of boron, gallium, aluminum and indium;

an irregular pattern including a plurality of recesses and projections being formed in the surface of said first nitride based semiconductor layer;

insulating films respectively formed on the bottom ~~surface of a recess~~ surfaces of the recesses and the top ~~surface of a projection~~ surfaces of projections of said irregular pattern of said first nitride based semiconductor layer;

~~and~~ a second nitride based semiconductor layer formed on said insulating films and

containing at least one of boron, gallium, aluminum and indium; and

a third nitride based semiconductor layer formed on said second nitride based semiconductor layer, containing at least one of boron, gallium, aluminum and indium; and including an active region of the device.

**Claim 13 (Original)** The semiconductor device according to claim 12, wherein said second nitride based semiconductor layer includes an active layer.

**Claim 14 (Withdrawn)** A semiconductor device comprising:

an insulating substrate;

a first nitride based semiconductor layer formed on said insulating substrate and containing at least one of boron, gallium, aluminum and indium;

a plurality of striped insulating films formed a predetermined distance away from each other on said first nitride based semiconductor layer; and

a second nitride based semiconductor layer formed on said first nitride based semiconductor layer and said plurality of striped insulating films and containing at least one of boron, gallium, aluminum and indium,

said second nitride based semiconductor layer including an active region of the device above said plurality of striped insulating films.

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**Claim 15 (Withdrawn)** The semiconductor device according to claim 14, wherein said active region includes a light emitting portion.

**Claim 16 (Withdrawn)** The semiconductor device according to claim 15, wherein said second nitride based semiconductor layer has a striped current injection region for injecting a current into said light emitting portion, and said second nitride based semiconductor layer comprises a pair of cavity facets perpendicular to said striped current injection region.

**Claim 17 (Withdrawn)** The semiconductor device according to claim 15, wherein said plurality of striped insulating films are formed along a  $\langle 11\bar{2}0 \rangle$  direction of said first nitride based semiconductor layer.

**Claims 18-21 (Canceled)**